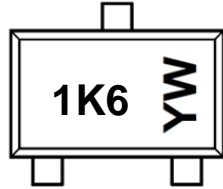
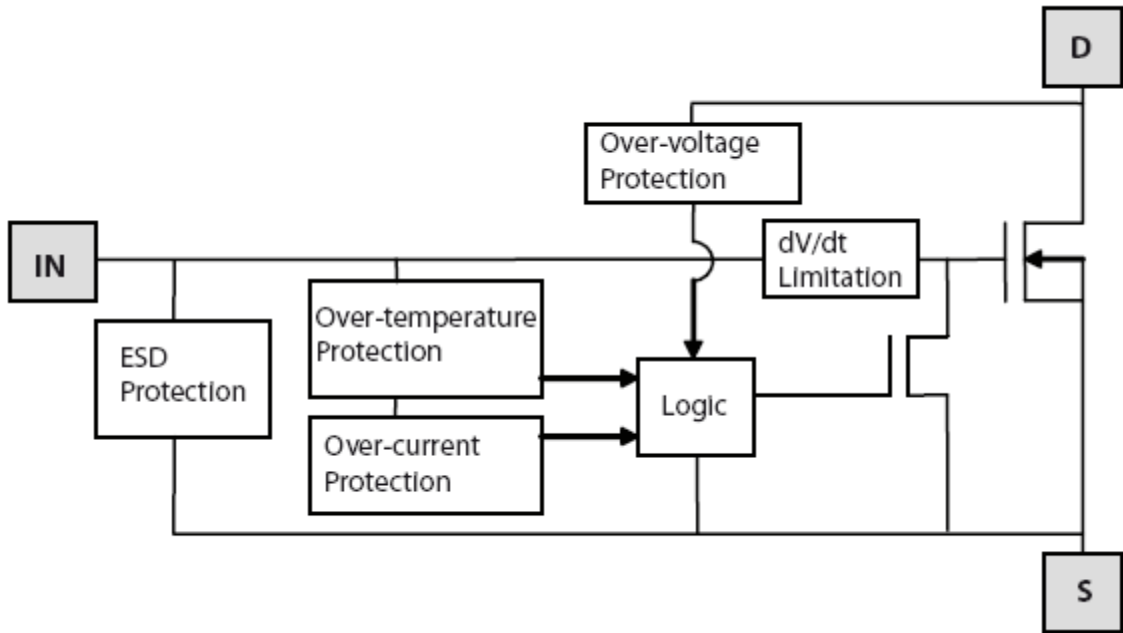


**Marking Information**



1K6 = Product Type Marking Code  
 Y or  $\bar{Y}$ : Year: 0 to 9 (ex: 2 = 2022)  
 W or  $\bar{W}$ : Week: A to Z: Week 1 to 26  
           a to z: Week 27 to 52  
           z: Represents Week 52 & 53

**Functional Block Diagram**



**Absolute Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Continuous Drain-Source Voltage	V <sub>DS</sub>	60	V
Drain-Source Voltage for Short Circuit Protection	V <sub>DS(SC)</sub>	36	V
Continuous Input Voltage	V <sub>IN</sub>	-0.5 ... +6	V
Continuous Input Current @ -0.2V ≤ V <sub>IN</sub> ≤ 6V	I <sub>IN</sub>	No Limit  I <sub>IN</sub>   ≤ 2	mA
Continuous Input Current @ V <sub>IN</sub> < -0.2V or V <sub>IN</sub> > 6V			
Pulsed Drain Current @ V <sub>IN</sub> = 3.3V	I <sub>DM</sub>	2	A
Pulsed Drain Current @ V <sub>IN</sub> = 5V	I <sub>DM</sub>	2.5	A
Continuous Source Current (Body Diode)	I <sub>S</sub>	1	A
Pulsed Source Current (Body Diode)	I <sub>SM</sub>	5	A
Unclamped Single Pulse Inductive Energy T <sub>J</sub> = +25°C, I <sub>D</sub> = 0.5A, V <sub>DD</sub> = 24V	E <sub>AS</sub>	90	mJ
Electrostatic Discharge (Human Body Model)	V <sub>ESD</sub>	4,000	V
Charged Device Model	V <sub>CDM</sub>	1,000	V

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation @ T <sub>A</sub> = +25°C (Note 5)	P <sub>D</sub>	0.83	W
Linear Derating Factor		6.66	mW/°C
Power Dissipation @ T <sub>A</sub> = +25°C (Note 6)	P <sub>D</sub>	1.5	W
Linear Derating Factor		12.0	mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	150	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>θJA</sub>	83	°C/W
Thermal Resistance, Junction to Case (Note 7)	R <sub>θJC</sub>	44	°C/W
Operating Temperature Range	T <sub>J</sub>	-40 to +150	°C
Storage Temperature Range	T <sub>STG</sub>	-55 to +150	°C

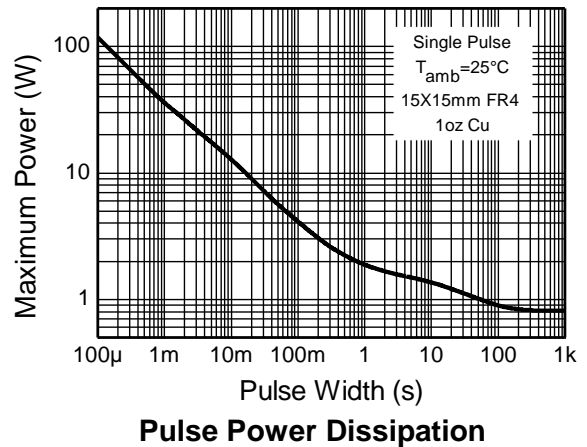
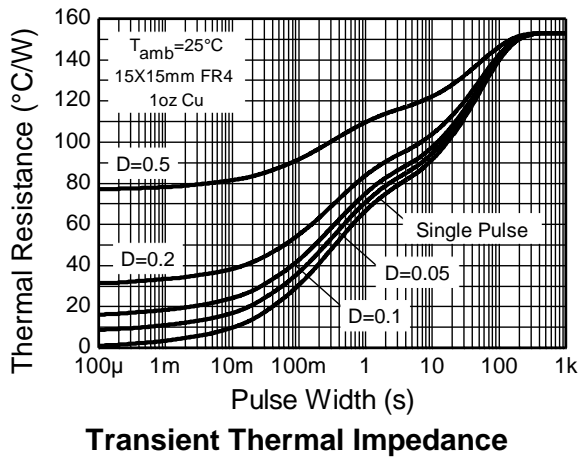
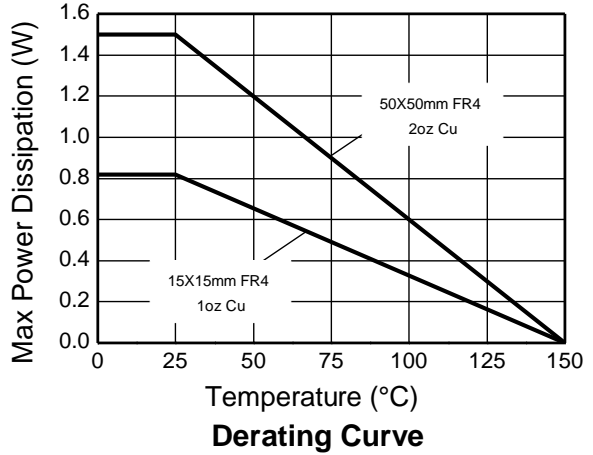
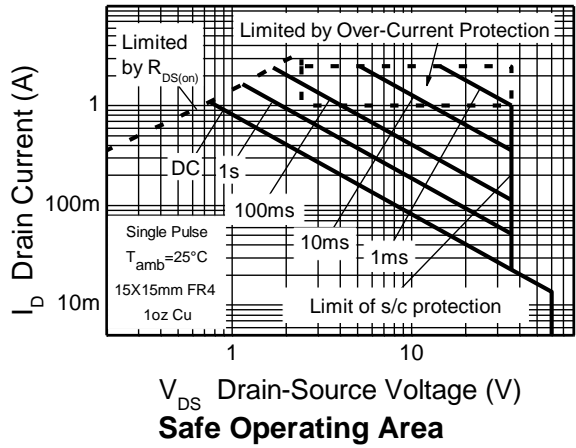
**Recommended Operating Conditions**

The ZXMS6004FF is optimized for use with μC operating from 3.3V and 5V supplies.

Characteristic	Symbol	Min	Max	Unit
Input Voltage Range	V <sub>IN</sub>	0	5.5	V
Ambient Temperature Range	T <sub>A</sub>	-40	+125	°C
High Level Input Voltage for MOSFET to be On	V <sub>IH</sub>	3	5.5	V
Low Level Input Voltage for MOSFET to be Off	V <sub>IL</sub>	0	0.7	V
Peripheral Supply Voltage (Voltage to Which Load is Referred)	V <sub>P</sub>	0	36	V

- Notes:
5. For a device surface mounted on 15mm x 15mm single sided, 1oz weight copper on 1.6mm FR4 board, in still air conditions.
  6. For a device surface mounted on 50mm x 50mm single sided, 2oz weight copper on 1.6mm FR4 board, in still air conditions.
  7. Thermal resistance from junction and the mounting surfaces of the drain pins.

**Typical Thermal Characteristics**

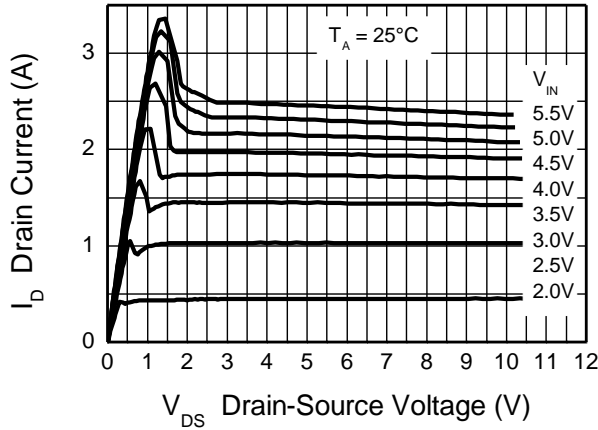


**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

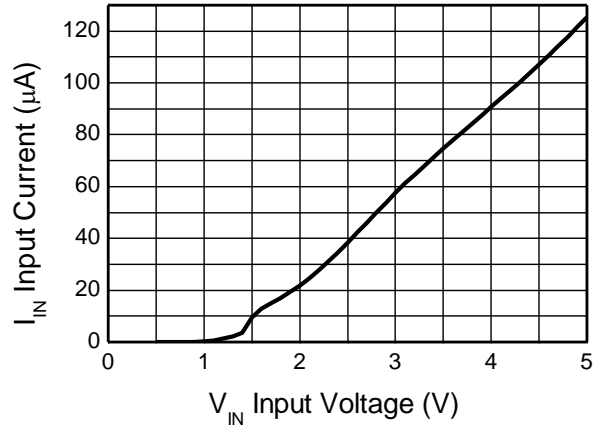
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>Static Characteristics</b>						
Drain-Source Clamp Voltage	V <sub>DS(AZ)</sub>	60	65	70	V	I <sub>D</sub> = 10mA
Off-State Drain Current	I <sub>DSS</sub>	—	—	500	nA	V <sub>DS</sub> = 12V, V <sub>IN</sub> = 0V
		—	—	1	μA	V <sub>DS</sub> = 36V, V <sub>IN</sub> = 0V
Input Threshold Voltage	V <sub>IN(TH)</sub>	0.7	1	1.5	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 1mA
Input Current	I <sub>IN</sub>	—	60	100	μA	V <sub>IN</sub> = +3V
		—	120	200		V <sub>IN</sub> = +5V
Input Current while Overtemperature Active	—	—	—	220	μA	V <sub>IN</sub> = +5V
Static Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	—	400	600	mΩ	V <sub>IN</sub> = +3V, I <sub>D</sub> = 0.5A
		—	350	500		V <sub>IN</sub> = +5V, I <sub>D</sub> = 0.5A
Continuous Drain Current (Note 5)	I <sub>D</sub>	0.9	—	—	A	V <sub>IN</sub> = 3V, T <sub>A</sub> = +25°C
		1.0	—	—		V <sub>IN</sub> = 5V, T <sub>A</sub> = +25°C
Continuous Drain Current (Note 6)		1.2	—	—		V <sub>IN</sub> = 3V, T <sub>A</sub> = +25°C
		1.3	—	—		V <sub>IN</sub> = 5V, T <sub>A</sub> = +25°C
Current Limit (Note 8)	I <sub>D(LIM)</sub>	0.7	1.7	—	A	V <sub>IN</sub> = +3V
		1	2.2	—		V <sub>IN</sub> = +5V
<b>Dynamic Characteristics</b>						
Turn-On Delay Time	t <sub>D(ON)</sub>	—	5	—	μs	V <sub>DD</sub> = 12V, I <sub>D</sub> = 0.5A, V <sub>GS</sub> = 5V
Rise Time	t <sub>R</sub>	—	10	—		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	45	—		
Fall Time	t <sub>F</sub>	—	15	—		
<b>Overtemperature Protection</b>						
Thermal Overload Trip Temperature (Note 9)	T <sub>JT</sub>	+150	+175	—	°C	—
Thermal Hysteresis (Note 9)	f <sub>F</sub>	—	+10	—	°C	—

- Notes:
5. For a device surface mounted on 15mm x 15mm single sided, 1oz weight copper on 1.6mm FR4 board, in still air conditions.
  6. For a device surface mounted on 50mm x 50mm single sided, 2oz weight copper on 1.6mm FR4 board, in still air conditions.
  7. Thermal resistance from junction and the mounting surfaces of the drain pins.
  8. The drain current is restricted only when the device is in saturation (see graph 'Typical Output Characteristic'). This allows the device to be used in the fully on-state without interference from the current limit. The device is fully protected at all drain currents, as the low power dissipation generated outside saturation makes current limit unnecessary.
  9. Overtemperature protection is designed to prevent device from destruction under fault conditions. Fault conditions are considered as "outside" normal operating range, so this part is not designed to withstand overtemperature for extended periods.

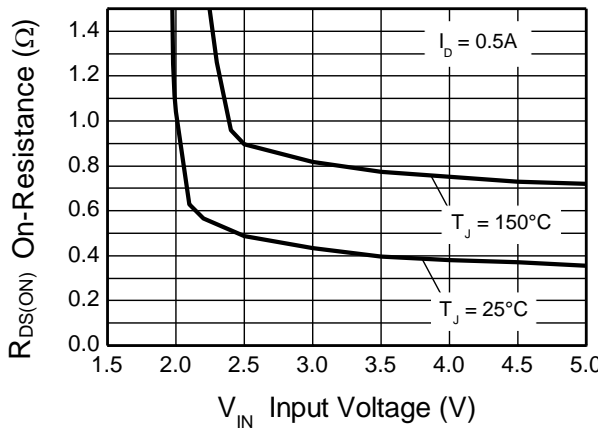
**Typical Performance Characteristics**



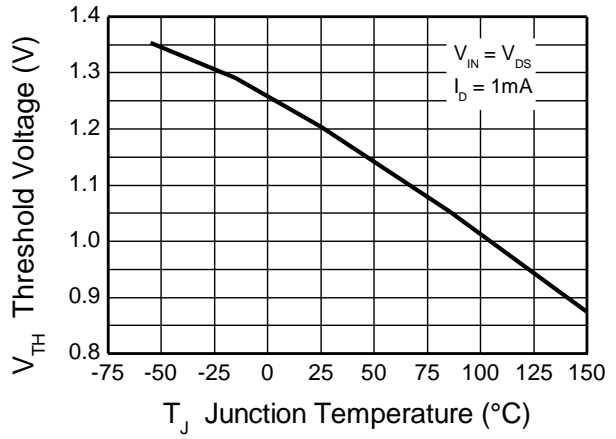
**Typical Output Characteristic**



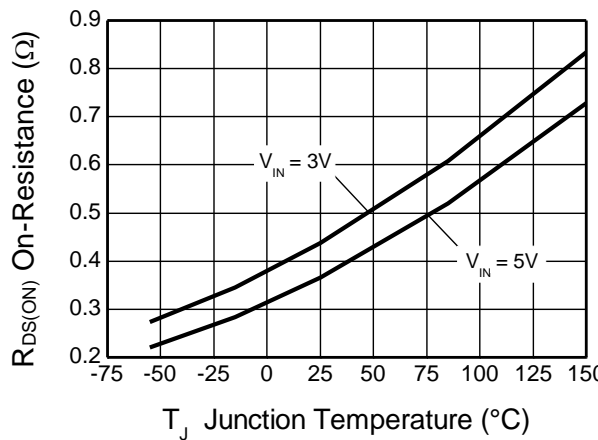
**Input Current vs Input Voltage**



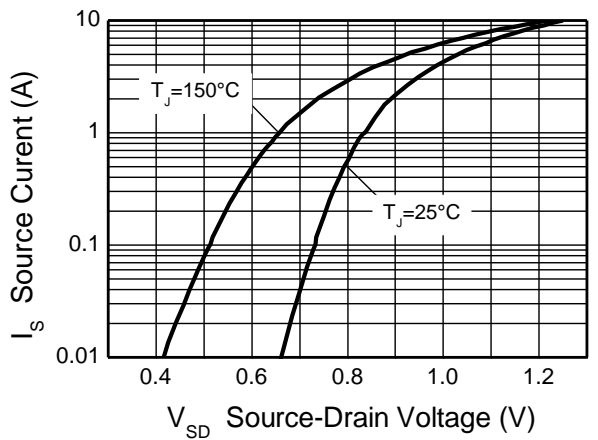
**On-Resistance vs Input Voltage**



**Threshold Voltage vs Temperature**

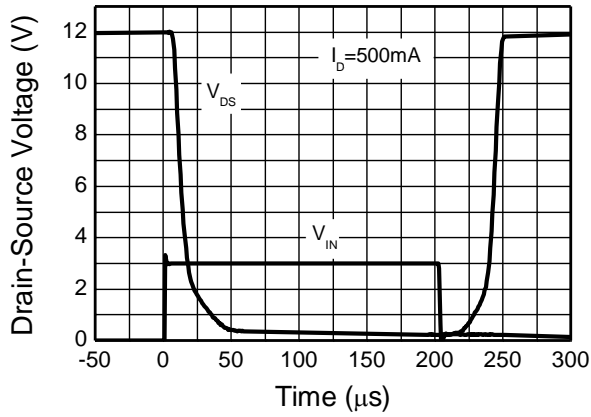


**On-Resistance vs Temperature**

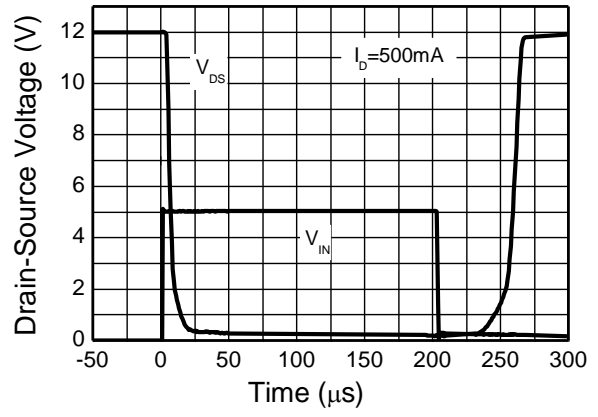


**Reverse Diode Characteristic**

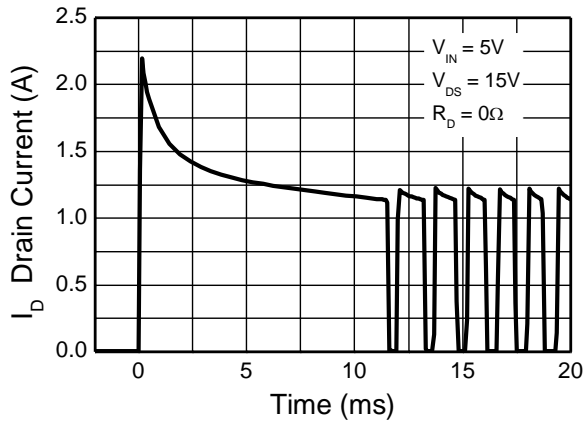
**Typical Performance Characteristics** (continued)



**Switching Speed**



**Switching Speed**

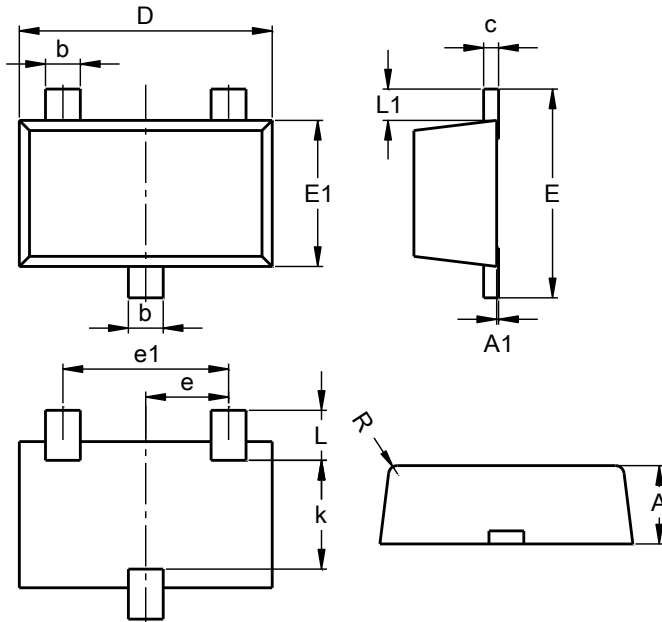


**Typical Short Circuit Protection**

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT23F**

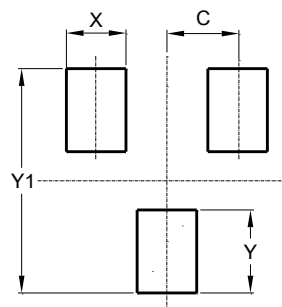


SOT23F			
Dim	Min	Max	Typ
A	0.80	1.00	0.90
A1	0.00	0.10	0.01
b	0.35	0.50	0.44
c	0.10	0.20	0.16
D	2.80	3.00	2.90
e	0.95 REF		
e1	1.90 REF		
E	2.30	2.50	2.40
E1	1.50	1.70	1.65
k	1.20	-	-
L	0.30	0.65	0.50
L1	0.30	0.50	0.40
R	0.05	0.15	-
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT23F**



Dimensions	Value (in mm)
C	0.95
X	0.80
Y	1.110
Y1	3.000

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